

ABSTRACT

A ferroelectric random access memory (FRAM) device, and a fabrication method therefor, includes seed layers above and below a ferroelectric layer. The seed layers formed above and below faces of the ferroelectric layer can prevent an imprint phenomenon from being generated in a ferroelectric capacitor by making the characteristics of the upper and lower interfaces of the ferroelectric layer be the same. This is accomplished by providing upper and lower seed layers that are crystallized prior to the ferroelectric layer during a thermal treatment. This results in crystallization occurring from the upper and lower faces to the center of the ferroelectric layer, making the characteristics of the upper and lower interfaces of the ferroelectric layer the same, thereby improving ferroelectric capacitor characteristics.